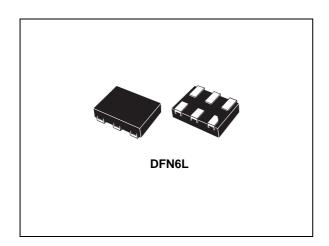
AS11P2TLR



Low voltage 1 Ω single-pole double-throw analog switch with breakbefore-make feature

Datasheet - production data



Features

- High speed:
 - t_{PD} = 130 ps (typ.) at V_{CC} = 3.0 V
 - t_{PD} = 140 ps (typ.) at V_{CC} = 2.3 V
- Ultra low power dissipation:
 - I_{CC} = 0.2 μ A (max.) at T_A = 85 °C
- Low ON resistance:
 - R_{ON} = 1.0 Ω (typ.) at V_{CC} = 4.5 V
 - R_{ON} = 1.2 Ω (typ.) at V_{CC} = 3.0 V
 - R_{ON} = 2.0 Ω (typ.) at V_{CC} = 1.8 V
- Wide operating voltage range:
 - V_{CC} (opr.) = 1.65 to 4.5 V single supply
- 5 V tolerant and 1.8 V compatible threshold ON digital control input at V_{CC} = 1.65 to 4.5 V
- Latch-up performance exceeds 200 mA per JESD 78, Class II
- ESD performance tested per JESD 22
 - 2000 V human-body model (A114-B, Class II)
 - 200 V machine model (A115-A)
- 1000 V charged-device model (C101)

Description

The AS11P2TLR is a high speed CMOS low voltage single analog SPDT (single-pole double-throw) switch or 2:1 multiplexer/demultiplexer switch manufactured using silicon gate C²MOS technology. Designed to operate from a 1.65 to 4.5 V supply, this device is ideal for portable applications.

The device offers very low ON-resistance (1 Ω) at V_{CC} = 4.5 V. Switch S1 is ON (connected to common ports Dn) when the SEL input is held high, and OFF (state of high impedance exists between the two ports) when SEL is held low.

Switch S2 is ON (connected to common port D) when the SEL input is held low, and OFF (state of high impedance exists between the two ports) when SEL is held high.

Additional key features are fast switching speed, break-before-make delay time and ultralow power consumption. All inputs and outputs are equipped with protection circuits to protect against static discharge, giving them immunity from ESD and transient excess voltage.

Table 1. Device summary

Order code	Package	Packaging
AS11P2TLR	DFN6L (1.2 x 1 mm)	Tape and reel

Contents AS11P2TLR

Contents

1	Pin connections and functions
2	Electrical ratings
3	Electrical characteristics
	3.1 DC electrical characteristics
	3.2 AC electrical characteristics
	3.3 Analog switch characteristics
4	Test circuits
5	Package information
6	Revision history



1 Pin connections and functions

Figure 1. Pin connections (top through view)

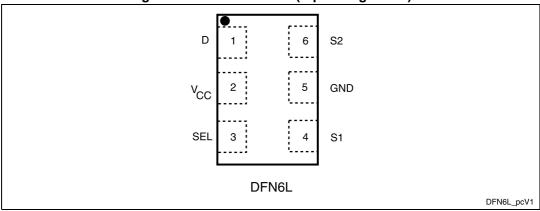


Table 2. Pin descriptions

Pin number	Symbol	Name and function
4	S1	Independent channel
6	S2	Independent channel
1	D	Common channels
3	SEL	Control
2	V _{CC}	Positive supply voltage
5	GND	Ground (0 V)

Figure 2. Input equivalent circuit

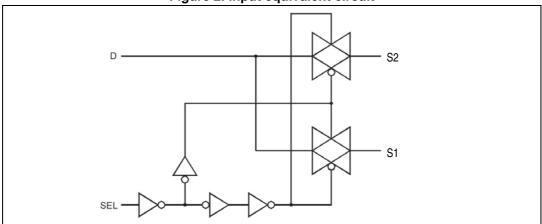


Table 3. Truth table

Sel	Switch S1	Switch S2
Н	ON	OFF ⁽¹⁾
L	OFF ⁽¹⁾	ON

^{1.} High impedance.



Electrical ratings AS11P2TLR

2 Electrical ratings

Stressing the device above the rating listed in *Table 4: Absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in *Table 5: Recommended operating conditions* of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronicsTM SURE program and other relevant quality documents.

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	-0.5 to 5.5	V
VI	DC input voltage	-0.5 to V _{CC} +0.5	V
V _{IC}	DC control input voltage	-0.5 to 5.5	V
V _O	DC output voltage	-0.5 to V _{CC} +0.5	V
I _{IKC}	DC input diode current on control pin (V _{SEL} < 0 V)	– 50	mA
I _{IK}	DC input diode current (V _{IN} < 0 V)	±50	mA
I _{OK}	DC output diode current	±20	mA
I _O	DC output current	±200	mA
I _{OP}	DC output current peak (pulse at 1 ms, 10% duty cycle)	±400	mA
I _{CC} or I _{GND}	DC V _{CC} or ground current	±100	mA
P _D	Power dissipation at T _A = 70 °C ⁽¹⁾	1120	mW
T _{STG}	Storage temperature	-65 to 150	°C
T _L	Lead temperature (10 s)	300	°C

^{1.} Derate above 70 °C by 18.5 mW/°C.

Table 5. Recommended operating conditions

Symbol	Paran	Value	Unit		
V_{CC}	Supply voltage		1.65 to 4.5	V	
V _I	Input voltage		0 to V _{CC}	V	
V _{IC}	Control input voltage	Control input voltage			
V _O	Output voltage	Output voltage			
T _{op}	Operating temperature		-40 to 85	°C	
dt/dv	Input rise and fall time	V _{CC} = 1.65 to 2.7 V	0 to 20	ns/V	
di/dv	control input	V _{CC} = 3.0 to 4.5 V	0 to 10	115/ V	

3 Electrical characteristics

3.1 DC electrical characteristics

Table 6. DC specifications

						Value			
Symbol	Parameter	V _{CC} (V)	Test condition	T,	λ = 25 °C	;	-40 to 8	85 °C	Unit
				Min.	Тур.	Max.	Min.	Max.	
		1.65 – 1.95		0.65 V _{CC}			0.65 V _{CC}		
		2.3 – 2.5		1.2			1.2		
V_{IH}	High level input voltage	2.7 – 3.0		1.3			1.3		V
		3.3 – 3.6		1.4			1.4		
		4.5		1.6			1.6]
		1.65 – 1.95				0.40		0.40	
		2.3 – 2.5				0.60		0.60]
V_{IL}	Low level input voltage	2.7 – 3.0				0.60		0.60	٧
	Vollage	3.3 – 3.6				0.60		0.60]
		4.5				0.80		0.80	
		1.8			2.0	3.0		3.5	
Б	Switch ON-	2.7	$V_S = 0 V \text{ to } V_{CC}$		1.3	1.6		1.8]
R _{ON}	resistance	3.0	I _S = 100 mA		1.2	1.5		1.7	Ω
		4.5			1.0	1.2		1.4	1
		1.8			0.06				
4.0	ON-resistance	2.7	V _S at R _{ON} max		0.05				
ΔR _{ON}	match between channels ⁽¹⁾	3.0	I _S = 100 mA		0.05				Ω
		4.5			0.05]
		1.8			1.0	1.5		1.5	
_	ON-resistance	2.7	$V_S = 0 V \text{ to } V_{CC}$		0.45	0.60		0.70	
R _{FLAT}	flatness ⁽²⁾	3.0	I _S = 100 mA		0.43	0.50		0.60	Ω
		4.5			0.39	0.50		0.60	1
l _{OFF}	OFF state leakage current (Sn), (D)	4.3	V _S = 0.3 or 4 V			±20		±100	nA
I _{IN}	Input leakage current	0 – 4.5	V _{SEL} = 0 to 4.5 V			±0.1		±1.0	μА
I _{CC}	Quiescent supply current	1.65 – 4.5	V _{SEL} = V _{CC} or GND			±0.1		±1.0	μА

Electrical characteristics AS11P2TLR

iumio di 2 di optioni di									
						Value			
Symbol	Parameter	V _{CC} (V)	Test condition	T,	₄ = 25 °C	;	-40 to 8	35 °C	Unit
				Min.	Тур.	Max.	Min.	Max.	
	Quiescent	4.3	V _{SEL} = 1.65 V		±17	±35		±70	
I _{CCLV}	supply current low voltage	4.3	V _{SEL} = 1.80 V		±15	±30		±60	μА
	driving	4.3	V _{SEL} = 2.60 V		±5	±10		±20	

Table 6. DC specifications (continued)

3.2 AC electrical characteristics

Table 7. AC electrical characteristics (C $_L$ = 35 pF, R $_L$ = 50 $\Omega,\,t_r$ = $t_f\,\leq\,$ 5 ns)

				00 p.		Value	<u> </u>		
Symbol	Parameter	V _{CC} (V)	Test conditions	-	Γ _A = 25 °	С	– 40 t	o 85 °C	Unit
		(-)		Min.	Тур.	Max.	Min.	Max.	
		1.65 – 1.95			0.15				
+ +	Propagation dolay	2.3 – 2.7			0.14				ne
t _{PLH} , t _{PHL}	Propagation delay	3.0 – 3.3			0.13				ns
		3.6 – 5.0			0.13				
		1.65 – 1.95	V _S = 0.8 V		36				
+.	Turn-ON time	2.3 – 2.7			31	40		45	ns
t _{ON}	Turr-ON time	3.0 – 3.3	V _S = 1.5 V		24	31		40	113
		3.6 – 5.0			21	28		32	
		1.65 – 1.95	V _S = 0.8 V		29				
+ .	Turn-OFF time	2.3 – 2.7			17	27		37	ns
t _{OFF}	rum-orr ume	3.0 - 3.3	V _S = 1.5 V		12	23		33	113
		3.6 – 5.0			11	21		31	
		1.65 – 1.95			15				
.	Break-before-	2.3 – 2.7	$C_L = 35 \text{ pF}$		10				ne
t _D	make time delay	3.0 – 3.3	$R_L = 50 \Omega$ $V_S = 1.5 V$		8				ns
		3.6 – 5.0			6				
		1.65			16				
Q	Charge injection	2.3	$C_L = 100 \text{ pF}$ $V_{GEN} = 0 \text{ V}$		22				pC
Q	Charge injection	3	$R_{GEN} = 0 V$		26				
		5.0			33				

^{1.} $\Delta R_{ON} = R_{ON(Max)} - R_{ON(Min)}$

^{2.} Flatness is defined as the difference between the maximum and minimum value of ON-resistance as measured over the specified analog signal ranges.

3.3 Analog switch characteristics

Table 8. Analog switch characteristics (C $_L$ = 5 pF, R $_L$ = 50 $\Omega,$ T $_A$ = 25 $^{\circ}C)$

						Value			
Symbol	Parameter	V _{CC} (V)	Test conditions	Т	A = 25 °	C	-40 to	85 °C	Unit
				Min.	Тур.	Max.	Min.	Max.	
OIRR	OFF isolation ⁽¹⁾	1.65 – 5.0	$V_S = 1 V_{RMS}$ f = 100 kHz		- 75				dB
Xtalk	Crosstalk	1.6 – 5.0	V _S = 1 V _{RMS} f = 100 kHz		- 80				dB
THD	Total harmonic distortion	2.3 – 5.0	$R_L = 600 \Omega$ $V_S = 2 V_{PP}$ f = 20 Hz to 20 kHz		0.03				%
BW	-3 dB bandwidth	1.65 – 5.0	$R_L = 50 \Omega$		150				MHz
C _{IN}	Control pin input capacitance				6				
C _{ON}	Sn port capacitance when switch is enabled	3.3	f = 1 MHz		52				
C _{OFF}	Sn port capacitance when switch is disabled	3.3	f = 1 MHz		25				pF
C _D	D port capacitance when switch is enabled	3.3	f = 1 MHz		50				

^{1.} OFF isolation = $20 \log_{10} (V_D/V_S)$, V_D = output. V_S = input to OFF switch.

Test circuits AS11P2TLR

Test circuits 4

Figure 3. ON resistance

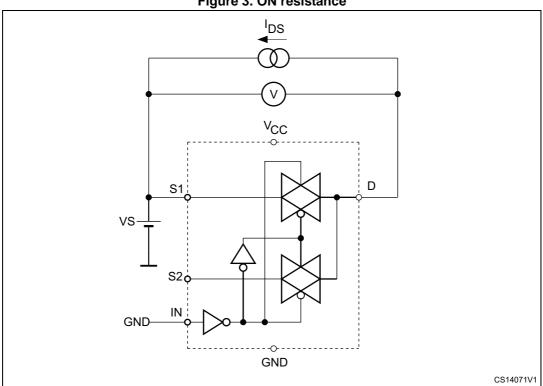
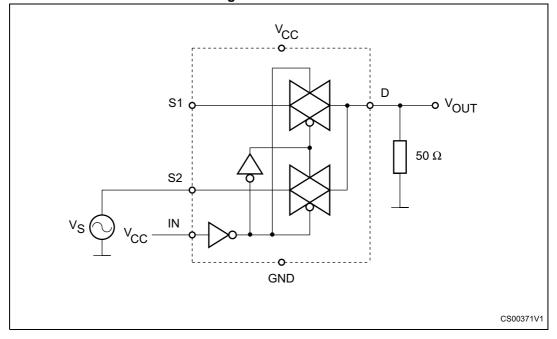


Figure 4. Bandwidth



AS11P2TLR Test circuits

Figure 5. OFF leakage

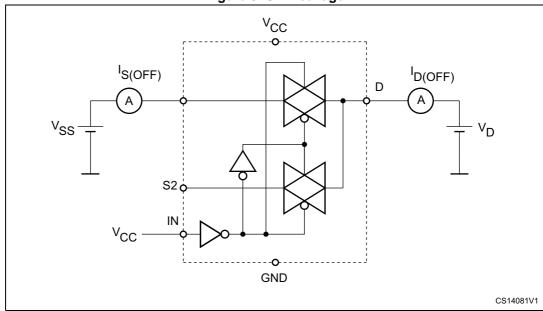
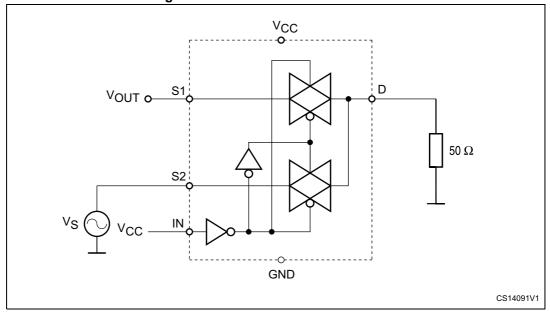


Figure 6. Channel-to-channel crosstalk



Test circuits AS11P2TLR

Figure 7. OFF isolation

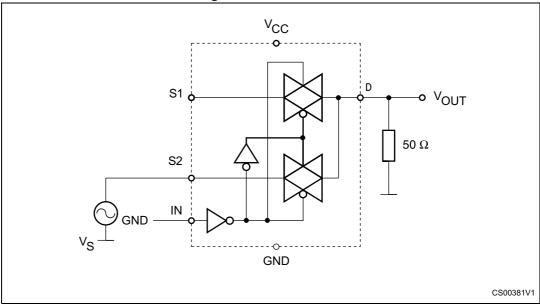
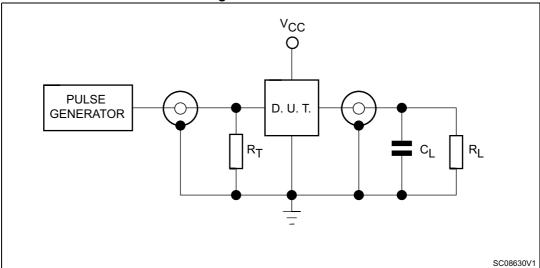


Figure 8. Test circuit



- 1. $C_L = 5/35$ pF or equivalent: (includes jig capacitance).
- 2. $R_L = 50 \Omega$ or equivalent.
- 3. $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω).

AS11P2TLR Test circuits

Figure 9. Break-before-make time delay

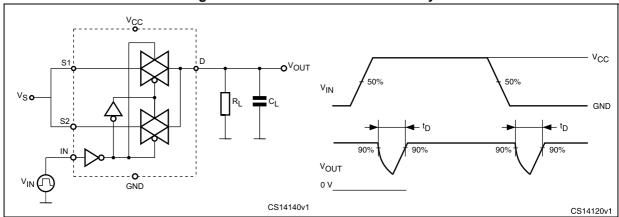


Figure 10. Switching time and charge injection (V_{GEN} = 0 V, R_{GEN} = 0 Ω , R_L = 1 M Ω , C_L= 100 pF)

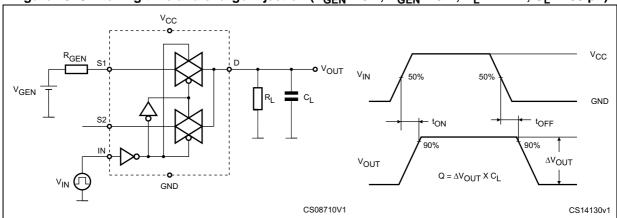
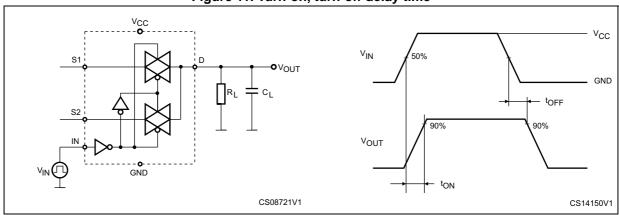


Figure 11. Turn-on, turn-off delay time



Package information AS11P2TLR

5 Package information

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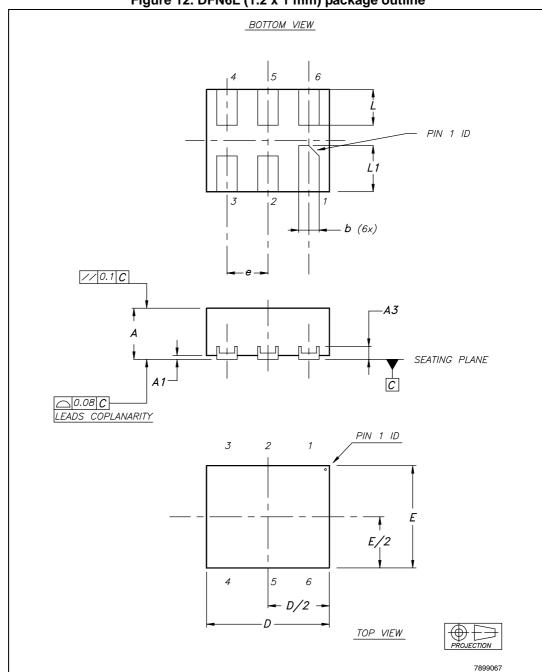


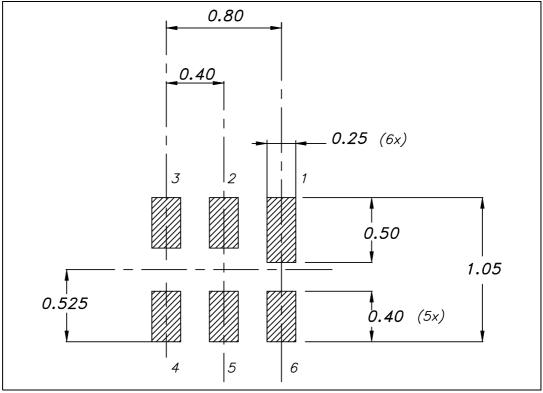
Figure 12. DFN6L (1.2 x 1 mm) package outline

1. Drawing is not to scale.

Table 9. DFN6L (1.2 x 1 mm) mechanical data

Cumbal	Dimensions (millimeters)					
Symbol	Тур.	Min.	Max.			
Α	0.50	0.45	0.55			
A1	0.02	0	0.05			
A3	0.127					
b	0.20	0.15	0.25			
D	1.20	1.15	1.25			
E	1	0.95	1.05			
е	0.40					
L	0.35	0.30	0.40			
L1	0.45	0.40	0.50			

Figure 13. DFN6L (1.2 x 1 mm) footprint recommendation



Package information AS11P2TLR

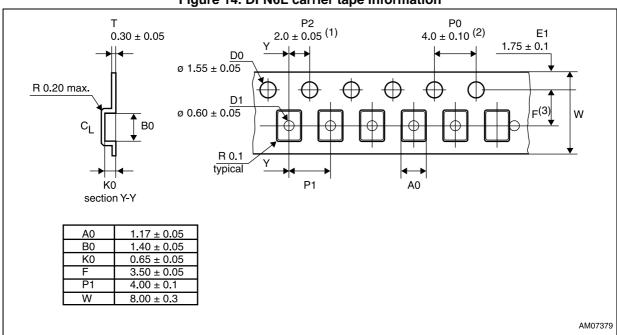


Figure 14. DFN6L carrier tape information

- 1. Measured from centreline of sprocket hole to centreline of pocket.
- 2. Cumulative tolerance of 10 sprocket holes is \pm 0.20.
- 3. Measured from centreline of sprocket hole to centreline of pocket.
- 4. Other material available.
- 5. Drawing is not to scale.
- 6. All dimensions are in millimeters unless otherwise stated.

AS11P2TLR Package information

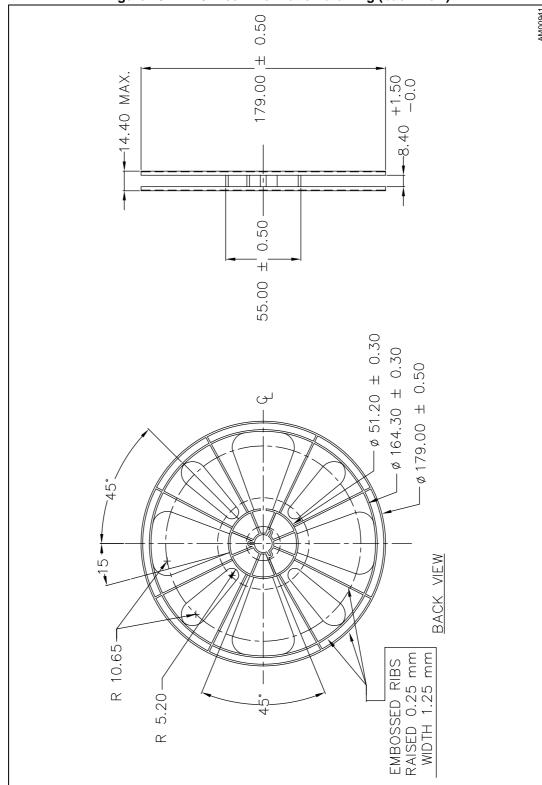


Figure 15. DFN6L reel information drawing (back view)

- 1. Drawing is not to scale.
- 2. Dimensions are in millimeters.

Package information AS11P2TLR

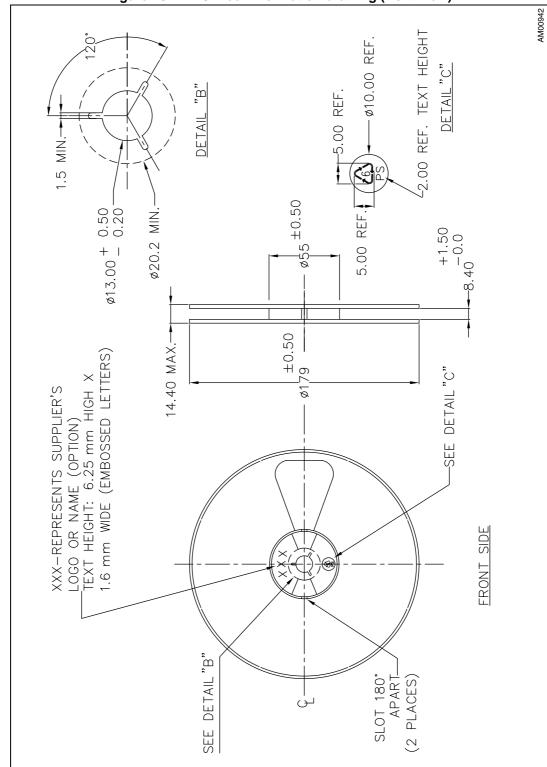


Figure 16. DFN6L reel information drawing (front view)

1. Drawing not to scale.

Dimensions are in millimeters.

AS11P2TLR Revision history

6 Revision history

Table 10. Document revision history

Date	Revision	Changes
07-Mar-2014	1	Initial release.

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